## NSN 5961-01-128-3316

**Fiig:** A110a0

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View Online at https://aerobasegroup.com/nsn/5961-01-128-3316 **Inclosure Material:** Plastic **Overall Length:** Between 0.300 inches and 0.330 inches **Overall Height:** Between 0.030 inches and 0.080 inches Overall Width: Between 0.240 inches and 0.290 inches **Component Name And Quantity:** 4 transistor **Mounting Method:** Press fit **Features Provided:** Burn in and hermetically sealed case **Semiconductor Material:** Silicon all transistor **Voltage Rating In Volts Per Characteristic:** 40.0 collector to base voltage/static/emitter open all transistor and 40.0 collector to emitter voltage/static/base open all transistor and 5.0 emitter to base voltage, static, collector open all transistor **Current Rating Per Characteristic:** 1.50 amperes source cutoff current all transistor **Power Rating Per Characteristic:** 4.0 watts small-signal input power, common-collector preset all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: pnp **Terminal Type And Quantity:** 14 ribbon Shelf Life: N/a **Unit Of Measure: Demilitarization:** Yes - demil/mli